

Guidelines for Preparation of Abstracts for EDISON 19 (Bold, 12 point, Times or Times New Roman)

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Camera-ready 1-page abstracts (including figures and references) should be prepared on an A4-size paper with 2 cm margins all around. The heading of the abstract must include the title of the paper, author(s), affiliation(s), address(es) and e-mail address. In the title, use capital letters for the initial letter of each word except articles, prepositions and conjunctions. Place a blank line between the title and author(s). The main text should be typed in single space and 11 point size. The list of numbered references should be at the end of the abstract in 9 point size. When referring to them in the text, the reference number should be indicated by brackets, such as [1, 2]. The deadline of the submission is **January 23, 2015**.

The 19th International Conference on Electron Dynamics in Semiconductors, Optoelectronics and Nanostructures (EDISON) will be held in Salamanca, Spain, from June 29 (Monday) through July 2



Fig.1. EDISON 19 logo (10 point)

(Thursday), 2015. Since the first meeting was held in Modena, Italy, in 1973, this series of meetings have been organized regularly; Modena, Italy (1973), Denton, USA (1977), Montpellier, France (1981), Innsbruck, Austria (1985), Boston, USA (1987), Scottsdale, USA (1989), Nara, Japan (1991), Oxford, UK (1993), Chicago, USA (1995), Berlin, Germany (1997), Kyoto, Japan (1999), Santa Fe, USA (2001), Modena, Italy (2003), Chicago, USA (2005), Tokyo, Japan (2007), Montpellier, France (2009), Santa Barbara, USA (2011) and Matsue, Japan (2013). EDISON 19 will highlight the latest progress in the field of fundamental physics and applications of electron dynamics in semiconductors, opto-electronic devices, and nanostructures.

The scope of EDISON 19 covers nonequilibrium and hot carrier dynamics in semiconductors, optoelectronics and nanostructure devices, with emphasis on the physics of transport and optical phenomena, including:

1. Nonequilibrium carrier transport in bulk and nanostructure systems
2. Coherent carrier dynamics in solids for quantum processing and communications
3. Coherent/incoherent carrier dynamics and ultra-fast optical phenomena
4. Terahertz phenomena in semiconductor materials and devices
5. Semiconductor-based spintronics
6. Carrier dynamics in organic materials
7. Electronic properties of graphene and graphene-based heterostructures
8. Ultrafast carrier dynamics in energy conversion processes
9. Nonequilibrium thermal transport in devices and nanostructures
10. Nonequilibrium carrier dynamics and fluctuations
11. Novel materials and devices

References

- [1] A. Iglesias and R. Vicente, *Appl. Phys. Lett.* **93**, 144519 (2011).
[2] S. Mendez, C. Ramos, and L. Egidio, *Phys. Rev. B* **73**, 076743 (2005).